

Serial No. 10/734,429

5. (Original) The thin film transistor array of claim 1 wherein the channel includes at least two bends such that a section of an electrode is surrounded on three sides by the channel in a U configuration.

6. (Withdrawn) The thin film transistor array of claim 1 wherein the channel completely surrounds one electrode.

7. (Original) The thin-film transistor array of claim 1 wherein the semiconductor used in the first thin-film transistor is an organic semiconductor.

8. (Original) The thin-film transistor array of claim 1 wherein the semiconductor used in the first thin-film transistor is a polymeric semiconductor.

9. (Withdrawn) The thin-film transistor array of claim 1 wherein the semiconductor is a continuous film over the array.

10. (Original) The thin film transistor array of claim 5 wherein the electrode is the drain electrode.

11. (Original) The thin-film transistor array of claim 1 wherein the pixel is backlit liquid crystal material.

12. (Currently Amended) The thin-film transistor array of claim 1 further comprising:

~~a gate line coupled to a gate electrode of the first thin film transistor; and,~~
a second thin film transistor including a corresponding gate electrode coupled to the gate line.

13. (Original) The thin film transistor array of claim 1 wherein the channel surrounds a drain electrode.

Serial No. 10/734,429

14. (Original) The thin film transistor array of claim 1 wherein the channel includes a first side and a second side, the first side of the channel coupled to the first electrode, the second side of the channel coupled to the second electrode.

15. (Original) The thin film transistor array of claim 1 wherein the first electrode is a drain and the second electrode is a source.

16. (Original) The thin film transistor of claim 14 wherein the channel includes a top surface, the top surface couples to a third electrode.

17. (Original) The thin film transistor of claim 16 wherein the third electrode is a gate.

18. (Withdrawn) The thin-film transistor array of claim 1 wherein the channel completely surrounds a source electrode.

19. (cancelled)

20. (Original) The thin-film transistor array of claim 19 further comprising:
a second thin film transistor to address a second pixel, the first data line coupled to a source electrode of the second thin film transistor.

21. (Original) The thin film transistor array of claim 20 further comprising:
a second pixel addressed by the second thin film transistor, the second pixel having two dimensions including a second pixel length and a second pixel width, a channel width of the second thin film transistor greater than the smallest dimension of the second pixel.

22. (Previously presented) The thin-film transistor array of claim 1 wherein the mobility of a semiconductor used to form the thin film transistor is below 0.5 cm²/Volt - second.

Serial No. 10/734,429

23. (Original) The thin-film transistor array of claim 1 further comprising:
 - a first gate line coupled to a gate electrode of the first thin-film transistor;
 - a second gate line coupled to a gate of a second thin-film transistor, the second-thin film transistor coupled to a second pixel; and,
 - a third gate line coupled to a gate electrode of a third thin-film transistor, the third-thin film transistor coupled to a third pixel.
24. (Original) The thin-film transistor array of claim 23 further comprising:
 - a drive circuit coupled to corresponding gate lines of each thin-film transistor, the drive circuit to switch each thin-film transistor to create a pattern in a display.
25. (Original) The thin-film transistor array of claim 23 further comprising:
 - a sensing circuit coupled to each gate line to sense the output of each thin-film transistor in a sensor system.
26. (Original) The thin film transistor array of claim 1 wherein the channel width to length ratio exceeds 50.
27. (Cancelled)
28. (Cancelled)
29. (Cancelled)
30. (Cancelled)
31. (Cancelled)
32. (Cancelled)